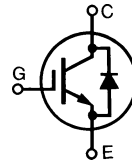


HiPerFAST™ IGBT with Diode

IXGH 20N60BD1
IXGT 20N60BD1

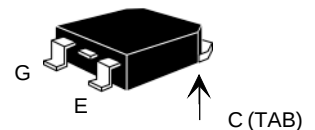
$$\begin{aligned} V_{CES} &= 600 \text{ V} \\ I_{C25} &= 40 \text{ A} \\ V_{CE(sat)typ} &= 1.7 \text{ V} \\ t_{fi(typ)} &= 100 \text{ ns} \end{aligned}$$

Preliminary data

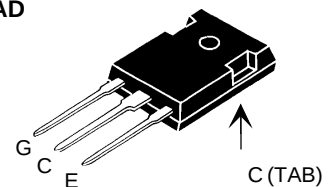


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	40	A
I_{C90}	$T_C = 90^\circ\text{C}$	20	A
I_{CM}	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	80	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 22 \Omega$ Clamped inductive load, $L = 100 \mu\text{H}$	$I_{CM} = 40$ @ $0.8 V_{CES}$	A
P_C	$T_C = 25^\circ\text{C}$	150	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque (M3) TO-247AD	1.13/10	Nm/lb.in.
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
Weight	TO-247AD	6	g
	TO-268	4	g

TO-268
(IXGT)



TO-247 AD
(IXGH)



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- International standard packages
- High frequency IGBT and antiparallel FRED in one package
- High current handling capability
- HiPerFAST™ HDMOS™ process
- MOS Gate turn-on -drive simplicity

Applications

- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

Advantages

- Space savings (two devices in one package)
- High power density
- Suitable for surface mounting
- Very low switching losses for high frequency applications
- Easy to mount with 1 screw, TO-247 (insulated mounting screw hole)

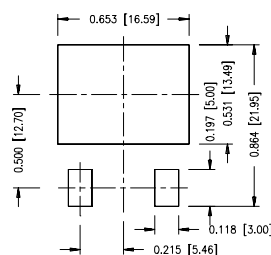
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 250 \mu\text{A}, V_{GE} = 0 \text{ V}$	600		V
$V_{GE(th)}$	$I_C = 250 \mu\text{A}, V_{CE} = V_{GE}$	2.5		5.5 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$ $T_J = 25^\circ\text{C}$ $T_J = 150^\circ\text{C}$			200 μA 3 mA
I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}, V_{GE} = 15 \text{ V}$	1.7	2.0	V

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$I_C = I_{C90}, V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$	9	17	S
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		1500	pF
C_{oes}			150	pF
C_{res}			40	pF
Q_g	$I_C = I_{C90}, V_{GE} = 15\text{ V}$, $V_{CE} = 0.5 V_{CES}$		55	nC
Q_{ge}			12	nC
Q_{gc}			20	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C90}, V_{GE} = 15\text{ V}$, $L = 100\text{ }\mu\text{H}$, $V_{CE} = 0.8 V_{CES}$, $R_G = R_{off} = 10\text{ }\Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$, higher T_J or increased R_G		15	ns
t_{ri}			25	ns
$t_{d(off)}$			110	200 ns
t_{fi}			100	150 ns
E_{off}			0.7	1.0 mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C90}, V_{GE} = 15\text{ V}$, $L = 100\text{ }\mu\text{H}$ $V_{CE} = 0.8 V_{CES}$, $R_G = R_{off} = 10\text{ }\Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$, higher T_J or increased R_G		15	ns
t_{ri}			35	ns
E_{on}			0.75	mJ
$t_{d(off)}$			220	ns
t_{fi}			140	ns
E_{off}			1.2	mJ
R_{thJC}	TO-247			0.83 K/W
R_{thCK}			0.25	K/W

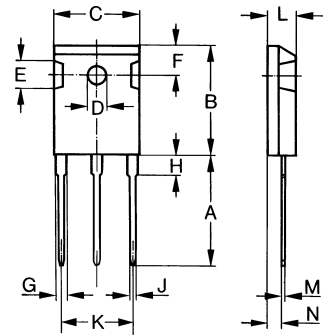
Reverse Diode (FRED)

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_F	$I_F = 30\text{ A}$, $V_{GE} = 0\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $d \leq 2\%$	$T_J = 150^\circ\text{C}$		1.6 V
		$T_J = 25^\circ\text{C}$		2.5 V
I_{RM}	$I_F = 30\text{ A}$, $V_{GE} = 0\text{ V}$, $-di_F/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}$ $I_F = 1\text{ A}$; $-di/dt = 100\text{ A}/\mu\text{s}$; $V_R = 30\text{ V}$		6	A
t_{rr}		$T_J = 100^\circ\text{C}$	100	ns
		$T_J = 25^\circ\text{C}$	25	ns
R_{thJC}				1.0 K/W

Min. Recommended Footprint

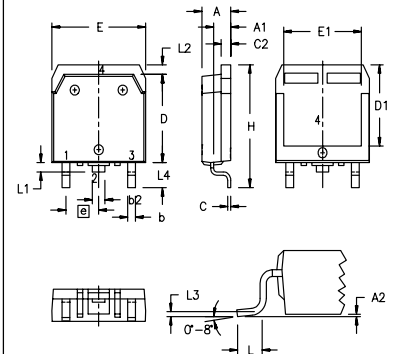


TO-247 AD (IXGH) Outline



Dim.	Millimeter Min. Max.	Inches Min. Max.
A	19.81 20.32	0.780 0.800
B	20.80 21.46	0.819 0.845
C	15.75 16.26	0.610 0.640
D	3.55 3.65	0.140 0.144
E	4.32 5.49	0.170 0.216
F	5.4 6.2	0.212 0.244
G	1.65 2.13	0.065 0.084
H	- 4.5	- 0.177
J	1.0 1.4	0.040 0.055
K	10.8 11.0	0.426 0.433
L	4.7 5.3	0.185 0.209
M	0.4 0.8	0.016 0.031
N	1.5 2.49	0.087 0.102

TO-268AA (D³ PAK)



Dim.	Millimeter Min. Max.	Inches Min. Max.
A	4.9 5.1	.193 .201
A ₁	2.7 2.9	.106 .114
A ₂	.02 .25	.001 .010
b	1.15 1.45	.045 .057
b ₂	1.9 2.1	.75 .83
C	.4 .65	.016 .026
D	13.80 14.00	.543 .551
E	15.85 16.05	.624 .632
E ₁	13.3 13.6	.524 .535
e	5.45 BSC	.215 BSC
H	18.70 19.10	.736 .752
L	2.40 2.70	.094 .106
L ₁	1.20 1.40	.047 .055
L ₂	1.00 1.15	.039 .045
L ₃	0.25 BSC	.010 BSC
L ₄	3.80 4.10	.150 .161

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